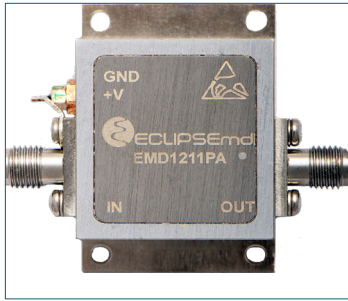


# EMD1211PA-02 Driver Amplifier Module

1 Watt Power Amplifier, DC-2 GHz



## Technical Characteristics

### Product Features

- 13.2 dB Gain @ 2 GHz
- +30.0 dBm Psat Output Power @ 2 GHz
- +27.5 dBm Output Power @ 2 GHz
- +12V @ 300 mA Typical Supply Voltage
- Low Cost Connectorized Module

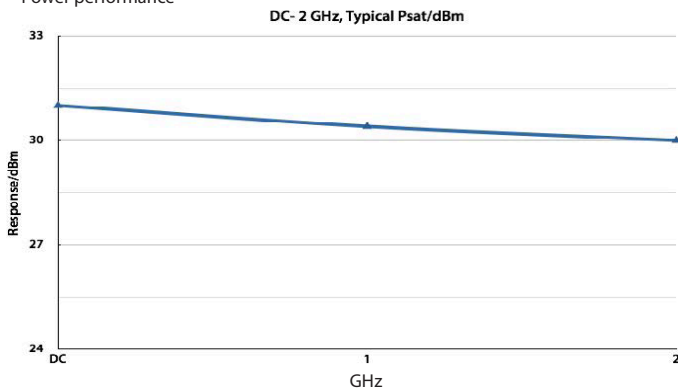
### Product Description

EclipseMDI Products EMD1211PA-02 is an GaAs MMIC amplifier module operating from DC to 2 GHz. This amplifier module is ideal for applications that requires a typical output of +30 dBm @ 2 GHz, while requiring only 300mA from a + 12 volt supply. Gain flatness of this device is typically  $\leq 0.7$  dB from DC to 2 GHz. The EMD1211PA-02 comes in a small connectorized module ideal for commercial and industrial applications.

## Electrical Specifications @ +25°C, Vdd=12V, Ids=300mA

Parameters	Freq. (GHz)	Min.	Typical	Max.	Units
Gain	DC	13.5	14.5		dB
	1.0	12.9	13.9		dB
	2.0	12.2	13.2		dB
Gain Flatness	DC to 2.0 GHz		$\pm 0.7$	$\pm 0.9$	dB
Gain Variation Over Temperature				0.005	dB/°C
Noise Figure			6.5		dB
Input Return Loss		12.0	14.0		dB
Output Return Loss		12.0	14.0		dB
1dB Compression Point	DC	27.0	28.0		dBm
	1.0	27.0	28.0		dBm
	2.0	26.0	27.0		dBm
Saturated Output Power	DC	31.0	32.0		dBm
	1.0	29.4	30.4		dBm
	2.0	29.0	30.0		dBm
3rd Order Intercept Point	DC		38.0		dBm
	1.0		38.0		dBm
	2.0		38.0		dBm

### Power performance



### About EclipseMDI

ECLIPSE Microdevices is located in San Jose, California. ECLIPSE has been developing high performance analog semiconductors for use in wireless radio frequency (RF), microwave, and millimeter wave for commercial and industrial applications. ECLIPSE has formed a strategic alliances - with foundries that features leading state-of-the-art process technologies and with manufacturing facilities for high-volume production of innovative RFIC's.

### Mechanical Drawing

